Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		(test\$3 near (memory semiconductor circuit)) and (first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:11
L1	1	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/746.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
L2	57	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/718.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
L3	63	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/724.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
L4	24	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/727.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON	2005/01/18:18:09
L5	6	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/730.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
L6	8	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/742.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
L7	22	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/738.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:10
S1	2	"5668764".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON	2004/02/23 13:11

S2	2	"5668764".pn. and (integrated cirucit device internal plurality signal signals select\$3 control\$4 path paths external\$2 input output pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 13:12
S3	2	"5668764":pn. and (integrated cirucit device internal plurality signal signals select\$3 control\$4 path paths external\$2 input output pad pads)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23:15:54
S4	1896	((flag near indicat\$3) error\$2) near (header)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2004/02/23 15:55
S5	2	"5668764".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	OFF	2004/02/25 14:40
S6	1309	(test\$3 near (memory semiconductor circuit)) and ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:12
S7	1948	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON	2005/01/18 18:08
S8	212	((test\$3 monitor\$3) near (memory semiconductor circuit)) same ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:12
S9	22	(((test\$3 monitor\$3) near (memory semiconductor circuit)) same ((first and second) near (select\$3))) and ((input output) near (pads))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON	2005/01/18 17:24
S10	105	(((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3))) and ((input output) near (pads))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:24